



**UNIVERSITI PUTRA MALAYSIA**

**EFFECT OF AGING AND HEAT TREATMENT ON THE OPTICAL  
PROPERTIES OF ZnS, SnS AND Se THIN FILMS**

**ABUBAKER ELSHIEKH ABDELRAHMAN**

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PROPERTIES OF ZnS, SnS AND Se THIN FILMS**

**By**

**ABUBAKER ELSHIEKH ABDELRAHMAN**

**Thesis Submitted in Fulfilment of the Requirement for the  
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**December 2000**



Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirement for the degree of Master of Science.

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**Chairman : Associate Professor Dr. Hj. W. Mahmood Mat Yunus, Ph.D.**

**Faculty : Science and Environmental**

Study on the optical properties of ZnS, SnS and Se thin films in polycrystalline and amorphous structure was carried out at room temperature. Double beam UV-spectrophotometer was used to obtain the transmissions curve. The measurement of transmission for each sample was conducted in the range of 300 to 1100 nm, and the structures of samples were analyzed using X-ray diffraction spectrometer. Swanepoel (1983) method had been used in this study to determine the optical properties of the ZnS, SnS and Se thin films.

Data from theoretical calculation was also used to cross-check the validity of the optical data of the samples. The results show that the refractive index of the samples decreases as wavelength increases. The energy band gaps of the samples are in good agreement with the data reported in the literature previously. The results also show that the refractive index of the samples is thickness dependent. However, the energy band

gaps for all the samples were found to be independent of film thickness in the range of 370 up to 742 nm. While the energy band gaps of the Se thin films decreases with increasing film thickness.

Three procedures of measurement were investigated for the samples. First, measurements were done immediately on the samples after they were deposited. Second, the measurement of the samples was done after they were exposed to the air. Third, the effect of annealing at different times in addition to different temperatures in ranging from (40 - 120) °C in ambient atmospheric pressure was studied. The results indicated that, the refractive index decreased with increasing the wavelength in all cases.

Other results in the present study indicate that the aging have more significant effect on the refractive index, plasma energy and energy band gap of the ZnS and Se samples. Furthermore the refractive index and the energy band gap of the a-ZnS were not affected with the annealing time, while the energy band gap of the SnS was affected with annealing temperature.

Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Master Sains.

**KESAN PEAUAAN DAN HABA KE ATAS SIFAT OPTIK  
FILEM NIPIS ZnS, SnS dan Se.**

**Oleh**

**ABUBAKER EL SHEIKH ABD EL RAHMAN**

**Disember 2000**

**Pengerusi : Profesor Madya Dr. Hj. W. Mahmood Mat Yunus, Ph.D.**

**Fakulti : Sains dan Pengajian Alam Sekitar**

Kajian sifat optik filem nipis ZnS, SnS dan Se dalam bentuk struktur polihabur dan amorfosnya telah dilakukan pada suhu bilik. UV-spektrofotometer dua-alur digunakan untuk memperolehi taburan spektrum transmisi. Pengukuran ke atas filem-filem nipis ini dibuat dalam julat jarak gelombang 300 hingga 1100 nm. Struktur filem-filem ini pula dikaji dengan menggunakan spektrometer pembiasan sinar-X. Kaedah Swanepoel (1983) telah digunakan dalam kajian ini untuk menentukan sifat optik bagi filem-filem nipis ZnS, SnS dan Se.

Pengiraan juga telah dibuat untuk menguji ketepatan data yang diperolehi. Keputusan menunjukkan bahawa indek pembiasan filem-filem berkurang apabila jarak gelombang bertambah. Data jalur tenaga terlarang yang diperolehi amat menyetujui dengan nilai yang telah dilaporkan oleh penyelidik-penyelidik lain. Keputusan juga menunjukkan bahawa nilai indek pembiasan bergantung kepada ketebalan sampel. Akan tetapi, tenaga jalur bagi filem-filem ini didapati tidak bergantung kepada ketebalan

sampel sehingga 742 nm. Bagi ketebalan sampel Se yang melebihi 742 nm, tenaga jalur terlarang berkurang dengan penambahan ketebalan sampel.

Tiga langkah pengukuran telah dilakukan untuk mengkaji filem-filem ini iaitu pertama, pengukuran dibuat sebaik sahaja siap disediakan. Kedua, pengukuran dibuat selepas filem-filem terdedah kepada udara. Ketiga, mengkaji kesan pemanasan pada tekanan atmosfera tetapi pada masa dan suhu (40 - 120) °C yang berlainan. Keputusan menunjukkan bahawa nilai indeks biasan berkurang dengan peningkatan jarak gelombang.

Hasil keputusan yang lain menunjukkan bahawa kesan penuaan memberikan kesan yang lebih ketara pada indeks biasan, tenaga plasma dan tenaga jalur. Nilai indeks biasan dan tenaga jalur pada sampel ZnS dan Se. Tambahan pula, indeks biasan dan tenaga jalur terlarang bagi a-ZnS menunjukkan ia tidak dipengaruhi oleh masa pemanasan, manakala tenaga jalur bagi SnS dipengaruhi oleh suhu pemanasan.

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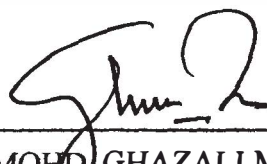
I certify that an Examination Committee met on 21,December, 2000 to conduct the final examination of Abubaker El Shiekh Abdelrahman on his Master of Science thesis entitled "Effect of Aging and Heat Treatment on the Optical Properties of ZnS, SnS and Se Thin Films" in accordance with Universiti Pertanian Malaysia (Higher Degree) Act 1980 and Universiti Pertanian Malaysia (Higher Degree) Regulations 1981. The Committee recommends that the candidate be awarded the relevant degree. Members of the Examination Committee are as follows:

Mohd Maarof Moxsin, Ph.D.  
Associate Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Chairman)

W. Mahmood Mat Yunus, Ph.D.  
Associate Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)

Zainal Abidin Talib, Ph.D.  
Associate Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)

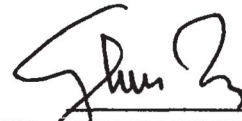
Zulkarnain Zainal, Ph.D.  
Associate Professor  
Faculty of Science and Environmental Studies  
Universiti Putra Malaysia  
(Member)

  
\_\_\_\_\_  
MOHD GHAZALI MOHAYIDIN, Ph.D,  
Professor /Deputy Dean of Graduate School,  
Universiti Putra Malaysia

Date: 12 JAN 2001



This thesis submitted to the Senate of Universiti Putra Malaysia has been accepted as fulfilment of the requirement for the degree of Master of Science.



**MOHD. GHAZALI MOHAYIDIN, Ph.D.**  
Professor  
Deputy Dean of Graduate School  
Universiti Putra Malaysia

I hereby declare that the thesis is based on my original work except for quotations and citations, which have been duly acknowledged. I also declare that it has not been previously or concurrently submitted for any other degree at UPM or other institutions.

  
Abubaker El Shiekh

Date : 12/1/2001

## TABLE OF CONTENTS

	Page
<b>ABSTRACT</b>	ii
<b>ABSTRAK</b>	iv
<b>ACKNOWLEDGEMENTS</b>	vi
<b>APPROVAL SHEETS</b>	x
<b>TABLE OF CONTENTS</b>	xii
<b>LIST OF TABLES</b>	xiii
<b>LIST OF FIGURES</b>	xviii
<b>LIST OF SYMBOLS</b>	
 <b>CHAPTER</b>	 1
<b>I INTRODUCTION</b>	1
Objective	3
Thin Film	3
Optical Constant	4
Energy Band Gap	4
Direct and Indirect Band Gap Semiconductors	5
Plasma Energy	6
 <b>II LITRATURE REVIEW</b>	 8
Introduction	8
Effect of Temperature on the Structure	10
Effect of Temperature on the Optical Properties	13
 <b>III EXPERIMENTAL PROCEDURE</b>	 15
Sample Preparation	17
Cleaning Procedures	20
Thin Film Deposition	20
Preparation of the Sn <sub>55</sub> S <sub>45</sub> Polycrystalline	21
The Measurement Technique	22
Aging	23
Heat Treatment	23
Determination of the Refractive Index	26
Calculation of Film Thickness	30
Single Oscillator Model	31
Absorption Coefficient and Energy Band Gap	32
 <b>IV RESULTS AND DISCUSSION</b>	 33
Transmission Spectra	34

	Determination of Refractive Index and Film Thickness	45
	Effect of Aging and Heat-treatment on Refractive Index	52
	Plasma Energy	67
	Effect of aging and Heat-treatment on the Plasma Energy	67
	Effect of aging and Heat-treatment on the Energy Band Gap	72
	X-ray Diffraction of The Samples	85
V	CONCLUSION	90
	BIBLIOGRAPHY	94
	APPENDICES	
A	Sn <sub>55</sub> S <sub>45</sub> Polycrystalline	97
B	Calculation of Refractive Index of the Glass Substrate	98
C	Transmission Spectra of Thin Film	99
D	Summary of the Experimental Data of the Sample, Glass Substrate and the Correction Data of the Sample	102
E	Transmission Spectra as Function of Wavelength Showing the Effect of Aging, Annealing Time and Temperature	106
F	X-ray Data and the Standard Values	110
	VITA	119

## LIST OF TABLES

Table	Title	Page
3.1	Material and Method of Preparation.	19
3.2	Material in the Present Work and the Labels.	20
3.3	ZnS and Se Samples Exposed to Air	22
3.4	ZnS, SnS and Se Samples Heated at Constant Temperature.	23
3.5	ZnS and SnS Samples Heated at Constant Temperature	24
4.1	Calculation of the Refractive Index of Glass Substrate in Wavelength below 350 nm	44
4.2	Average Values of Refractive Index for ZnS Thin Films	52
4.3	Average Values of Refractive Index for Se Thin Films	53
4.4a	Summary of Refractive Index, Number of Fringe and Thickness of c-ZnS Thin Film	54
4.4b	Summary the Refractive Index, Number of Fringe and Thickness of a-ZnS Thin Films	55
4.4c	Summary the Refractive Index, Number of Fringe and Thickness of the Se Thin Films	55
4.5	Energy Band Gap of the ZnS Thin Films	76
4.6	Energy Band Gap of the Se Thin Films	77

## LIST OF FIGURES

Figure	Title	Page
1.1	Schematic Diagram of Direct and Indirect Band Gap Transition	6
2.2	Phase Diagram for SnS Compounds	13
3.1	Evaporation Chamber Used for Preparation Thin Film	16
3.2	schematic Diagram of Electron Gun System Used for Preparation ZnS, of (a) Designed of Work Electron Gun Apparatus (b) Focuses the Electron Gun Beam onto Material for Evaporation Thin Film	17
3.3	Schematic Diagram Used for Preparation the Polycrystalline Sn <sub>55</sub> S <sub>45</sub>	20
3.4	Schematic Diagram of the Annealing System Used in the Present Work	24
3.5	Schematic Diagram of Thin Film Deposited on Glass Substrate	25
3.6	Maximum and Minimum Point on Transmission Curve, Which was Used to Determined the Refractive Index for ZnS Thin Films	27
3.7	Maximum and Minimum Point on Transmission Curve, Which was Used to Determined the Refractive Index for a-ZnS Thin Films	27
3.8	Maximum and Minimum Point on Transmission Curve, Which was Used to Determined the Refractive Index for Se Thin Films	28
4.1a	Transmission Spectra of c-ZnS Thin Film and Glass Substrate	35
4.1b	Transmission Spectra of a-ZnS Thin Film and Glass Substrate	36
4.1c	Transmission Spectra of Se Thin Film and Glass Substrate	36
4.2a	Correction Transmission of c-ZnS Thin Film	37
4.2b	Correction Transmission of a-ZnS Thin Film	37
4.2c	Correction Transmission of Se Thin Film	38
4.3	Theoretical Calculation and Experimental Data in Transparent Region	38

4.4a	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region of Se Thin Film With Thickness of 480 nm	40
4.4b	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region of Se Thin Film With Thickness of 496 nm	41
4.4c	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region for Se Thin Film With Thickness of 658 nm	41
4.5a	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region for Sn <sub>55</sub> S <sub>45</sub> Thin Film With Thickness of 750 nm	41
4.5b	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region for Sn <sub>55</sub> S <sub>45</sub> Thin Film With Thickness of 900 nm	42
4.5c	Theoretical Calculation and the Experimental Data in Weakly Absorbing Region for Sn <sub>55</sub> S <sub>45</sub> Thin Film With Thickness of 1140 nm	43
4.6	Refractive Index of ZnS Thin Films	45
4.7a	Refractive Index of a-ZnS Thin Films	46
4.7b	Comparison of Refractive Index of ZnS Thin Film, with Reference Data	46
4.8	Refractive Index of Se Thin Films	47
4.9a	Refractive Index of SnS Thin Film Estimated from Theoretical Calculation of Thickness 750 nm	48
4.9b	Refractive Index of SnS Thin Film Estimated from Theoretical Calculation of Thickness 900 nm	48
4.10a	Plot $\delta/2$ Against $(n/\lambda)$ to Determine the Order Number and Thickness for c-ZnS Thin Film	50
4.10b	Plot $\delta/2$ Against $(n/\lambda)$ to Determine the Order Number and Thickness for a-ZnS Thin Film	50
4.10c	Plot $\delta/2$ Against $(n/\lambda)$ to Determine the Order Number and Thickness for Se Thin Film	51
4.11a	Refractive Index for ZnS, After the Samples Exposed to Air	58

4.11b	Refractive Index for Se, After the Samples Exposed to Air	58
4.11c	Refractive Index for c-ZnS After Annealed at Different Times	59
4.12a	Refractive Index as Function of Time (Days) for c-ZnS	59
4.12b	Refractive Index as Function of Time (Days) for a-ZnS	60
4.12c	Refractive Index as Function of Time (Days) for Se	60
4.13a	Refractive Index of the c-ZnS Thin Film After Sample Annealed at Different Time	61
4.13b	Refractive Index of the a-ZnS Thin Film After Sample Annealed at Different Time	61
4.13c	Refractive Index of the Se Thin Film After Sample Annealed at Different Time	62
4.14a	Refractive Index as Function of Annealing Time Hour for c-ZnS	62
4.14b	Refractive Index as Function of Annealing Times Hour for a-ZnS	63
4.14c	Refractive Index as Function of Annealing Times Hour for Se	63
4.15a	Refractive Index of c-ZnS Annealing at Different Temperature	64
4.15b	Refractive Index of a-ZnS Annealing at Different Temperature	64
4.16a	Refractive Index as Function of Annealing at Different Temperature for c-ZnS	65
4.16b	Refractive Index as Function of Annealing at Different Temperature for a-ZnS	65
4.17	Plot $1/(n^2-1)$ Against $h\nu^2$ to Determine the Plasma Energy of c-ZnS Thin Film	68
4.18	Plot $1/(n^2-1)$ Against $h\nu^2$ to Determine the Plasma Energy of Se Thin Film	69
4.19a	Plasma Energy Against Time (Days) for c-ZnS	69
4.19b	Plasma Energy Against Time (Days) for a-ZnS	70



4.20a	Plasma Energy Against Annealing Time (Hours) for-ZnS	70
4.20b	Plasma Energy Against Annealing Time (Hours) for a-ZnS	71
4.21a	Plasma Energy Against Annealing Temperature °C for c-ZnS	72
4.21a	Plasma Energy Against Annealing Temperature °C for a-ZnS	72
4.22a	Plot of a $(\alpha h\nu)^2$ as Function of Energy	73
4.22d	Plot of a $(\alpha h\nu)^2$ as Function of Energy	73
4.22c	Plot of a $(\alpha h\nu)^{0.5}$ as Function of Energy	74
4.22d	Plot of a $(\alpha h\nu)^{0.5}$ as Function of Energy	74
4.23a	Energy Band Gap as Function of Film Thickness For A and B Samples	75
4.23b	Energy Band Gap as Function of Film Thickness For Se Samples	75
4.24a	Energy Band Gap as Function of Time (days) for c-ZnS	78
4.24b	Energy Band Gap as Function of days for a-ZnS	79
4.24c	Energy Band Gap as Function of Days for Se	79
4.25a	Energy Band Gap as Function of Annealing Time for ZnS Thin Film	80
4.25b	Energy Band Gap as Function of Annealing Time for a-ZnS Thin Film	80
4.25c	Energy Band Gap as Function of Annealing Time for SnS Thin Film	81
4.25d	Energy Band Gap as Function of Annealing Time for Se Thin Film	81
4.26a	Energy Band Gap as Function of Annealing Temperature for c-ZnS Thin Film	82
4.26b	Energy Band Gap as Function of Annealing Temperature for a-ZnS Thin film	82

4.26c	Energy Band Gap as Function of Annealing Temperature for SnS Thin Film	83
4.27a	X-ray Pattern of c-ZnS Thin Film	86
4.27b	X-ray Diffraction of Sn <sub>55</sub> S <sub>45</sub> Solid	87
4.27c	X-ray Diffraction of Sn <sub>55</sub> S <sub>45</sub> Thin Film	88
4.27d	X-ray Diffraction of Se Thin Film	89

## LIST OF SYMBOLS

$a\text{-ZnS}$	Amorphous Zinc Sulfide
$c\text{-ZnS}$	Polycrystalline Zinc Sulfide
$a\text{-Se}$	Amorphous Selenium
$T$	Transmission of the Film
$T \%$	Transmission of the Film (percentage)
$T_u \%$	Experimental Data of Transmission (percentage)
$R_1 \%$	Reflection of Film-air Interface (percentage)
$R_2 \%$	Reflection of Film-substrate Interface (percentage)
$R_3 \%$	Reflection of Substrate-air Interface (percentage)
$T_s \%$	Transmission of Glass Substrate (percentage)
$d$	Film Thickness
$d_{\text{true}}$	True Film Thickness
$T_M$	Maximum Transmission
$T_m$	Minimum Transmission
$T_a$	Interference Free Transmission
$n$	Refractive Index of film
$n_{\text{true}}$	True Refractive Index of Film

$N^*$	Complex of Refractive Index
$s$	Refractive Index of Substrate
$n_o$	Refractive Index of Air
$\lambda$	Wavelength (nm)
$K$	Wave Vector
$h\nu$	Photon Energy (eV)
$\alpha$	Absorption Coefficient ( $\text{cm}^{-1}$ )
$\delta$	Integer Number
$m$	Number of Fringes
$E_g$	Energy Band Gap of the Film (eV)
$E_o$	Average Oscillator Energy (eV)
$E_d$	Dispersion Energy (eV)
$E_p$	Plasma Energy (eV)

## **CHAPTER I**

### **INTRODUCTION**

The optical properties of the material are related to the characteristics of the electromagnetic wave absorption and emission. The optical properties also play an important role in developing and understanding of the structural and electronic properties of semiconductors thin film. Nevertheless, the optical properties of thin film could be found from the amplitude and state of polarization of a light beam, in the form of the Fresnel coefficient of reflection and transmission.

This study focuses on optical properties of Zinc sulfide (ZnS), Tin sulfide (SnS) and selenium (Se) semiconductor in thin film form. These materials attract much attention at different phase due to various physical applications.

Zinc sulfide is currently used in flat-screen solid state displays and can be employed in the new generation of visible light emitting laser diode. High

durability ZnS found useful in harsh commercial and military environment (Carl and Francis 1980). Studies on X-ray photoelectron spectroscopy by Olga *et al.* (1997), found that ZnS formed adherent film to glass substrate. The adherent process was further developed to produce the metal sulfide thin film photographic. However, ZnS compound was found to exhibit insulating behavior as well. This phenomenon could be due to an increase in the metallic component of binding and a decrease in the ionic component (Abrikosov *et al.* 1969).

According to Mishra *et al.* (1989) and Zulkarnain *et al.* (1997), even though SnS compound is relatively less studied, it is a promising material for the production of low cost material for solar energy conversion. The phase diagram of the SnS formed monochalcogenides in addition to more complex compounds comprised mainly of SnS<sub>2</sub>, Sn<sub>2</sub>S<sub>3</sub> and Sn<sub>3</sub>S<sub>4</sub> compositions, depending on the temperature and percentage of the constituents. Also SnS and SnS<sub>2</sub> were found to be the most stable compound with regard to melting points of  $(855 \pm 5) ^\circ\text{C}$  for the case of the sulfur atoms between 10 - 48 % and 68 - 95 % respectively (Abrikosov *et al.* 1969).

Selenium is widely used in commercial applications for example xerography and image processing. Zishan *et al.* (1997) stated that pure selenium has short lifetime, however Kotkata and Abdel Wahab (1990) observed that light could enhanced the crystallization process of the amorphous Se, at low temperature. They also established that the increase of the crystal growth rate by light heating could be resulted from the reproduction of hole-electron pairs in the amorphous Se thin film.

## Objective

The aim of this study is to characterize the optical properties of ZnS, SnS and Se thin films. Double beam UV-spectrophotometer was used in this study to measure the transmission spectra. Also as the transmission curve for each sample was determined, the samples were considered homogenous and isotropic with uniform thickness. Studies on optical properties are limited to optical constants, plasma energy and band gap energy. The analyses were carried out based on transmission spectra. Therefore, the objectives of the present study were:

- 1 - To characterize the optical properties of ZnS, SnS, and Se thin films.
- 2 - To study aging effect and heat treatment on the optical properties of ZnS, SnS, and Se thin films.

## Thin film

Thin film material can be either of crystalline or amorphous structures. A single crystal structure contains atoms that arranged in periodic arrays. Polycrystalline material consists of a matrix of crystallites, each crystal is essentially a single crystal with a different crystal axis orientation to its neighbor. It gives rise to the periodic potential within which the electrons exist. On other hand amorphous materials contain conveniently bonded atoms, which are arranged in an open network. The bonded atoms correlate with each other in order up to the third or fourth nearest neighbors. The short-range order is directly responsible for measurable semiconductor properties, such as optical and electrical.

## Optical Constants

The theoretical and experimental investigations on the optical behavior of thin films deal primarily with optical constants. The optical properties of the amorphous and crystalline semiconductor materials can be described by complex refraction index,  $N^* = n - ik$ . The real and imaginary parts of  $N^*$  are termed as refractive index and absorption index. The  $n$  and  $k$  are referred to as the optical constants of the medium. Generally, the optical constants are photon energy dependent and exhibit in interband regions, where the electron transitions are dominant. The bound electrons, which are present in semiconductor compounds, can be described in terms of complex dielectric constant, as  $N^{*2} = \epsilon_1 - i\epsilon_2$ , where  $\epsilon_1$  and  $\epsilon_2$ , are the real and imaginary parts of dielectric.

## The Energy Band Gap

Optical thin film theory is based on the Maxwell macroscopic theory of electromagnetic waves, as applied to the propagation of light across the thin films. The basic electronic band is mainly concerned with excitation of electrons above the band gap. In this process, holes are left behind in the valence band. The electrons and the holes can be treated as charged quasi-particles that move through periodic lattice with an effective mass. According to Nasser *et al.* (1993) the band gap of semiconductor gives a best understanding of fundamental electronic structure of solid, and can determine whether the band gap is a direct or an indirect allowed transition. The measurements of the optical band gap can be



done in a simplest way by measuring the absorption edge. Generally, in the various absorption processes, the electrons and holes absorb both photons and phonons. The photons supply the required energy, while the phonons supply the required momentum. In such a situation, the lowest threshold of the band gap energy cannot be achieved for a process that involves only photon energy. However, in the direct transition, the photon-initiated transitions require a constant wave vector,  $k$ . On the other hand the indirect allowed transition in which the  $k$  vectors of initial and final states are different; the phonon-assisted transition can still conserve momentum.

### **Direct and Indirect Band Gap Semiconductors**

Semiconductor material can be divided into two main transition groups, namely direct and indirect gaps. When the vertical transitions between valence and conduction band are allowed, and the photons are only involved in this transition, the material is called direct band gap semiconductor. The direct transition occurred in ZnS, CdS, GaAs and InSb and many more compound III - V or II - V materials. On the other hand, when the transitions between the valence band and conduction band are not linear and the transition is associated with photon-phonon coupling, the materials are called indirect band gap semiconductors. This type is found in Si, Se, SnS and Ga semiconductor materials. This phenomenon is displayed in Figure 1.1.